## AMENDMENTS TO THE SPECIFICATION

In paragraph [0023]:

The present invention light-emitting device 1, 2, 3 can include one high thermal conductive layer 101, 201, 301 or a plurality of high thermal conductive layers. The forming method of the high thermal conductive layer 101, 201, 301 is selected from at least one method of: electroplating, electroforming, electrolysis plating, and arc evaporation. The high thermal conductive layer 101, 201, 301 comprises at least one material selected from a material group consisting of Cu, Al, Au, Ag, W, and alloys of these metals, or other substitute materials. The connection layer comprises at least one material selected from a material group consisting of indium tin oxide, GeAu, BeAu, Au, SiNx, SiO2, Cu, Ti, and Pd, or other substitute materials. The substrate 10, 20, 30 comprises at least one material selected from a material group consisting of Si, GaAs, Ge, Al2O3, glass, InP, and GaP, or other substitute materials. The light-emitting stack layer 14, 24, 32 comprises at least one material selected from a material group consisting of AlGaInP, AlInGaN, and AlGaAs series, or other substitute materials. The transparent adhesive layer 12 comprises at least one material selected from a material group consisting of ~~PI, BCB, and PFCB,~~ polyimide (PI), benzocyclobutene (BCB), and perfluorocyclobutane (PFCB), or other substitute materials. The conductive transparent adhesive layer 22 comprises at least one material selected from a material group consisting of intrinsically conducting polymer and polymer doped with a conductive material, or other substitute materials, wherein the conductive material comprises at least one material selected from a material group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, zinc tin oxide, Au, and Ni/Au, or other substitute materials. The first reaction layer 115, 215 comprises at least one material selected from a material group consisting of SiNx, Ti, and Cr, or other substitute materials. The second reaction layer 125, 225 comprises at least one material selected from a material group

consisting of SiNx, Ti, and Cr, or other substitute materials. The metal reflecting layer 11, 21 comprises at least one material selected from a material group consisting of In, Sn, Al Au, Pt, Zn, Ge, Ag, Ti, Pb, Pd, Cu, AuBe, AuGe, Ni, PbSn, and AuZn, or other substitute materials. The metal adhesive layer 31 comprises at least one material selected from a material group consisting of In, Sn, Al Au, Pt, Zn, Ge, Ag, Ti, Pb, Pd, Cu, AuBe, AuGe, Ni, PbSn, and AuZn, or other substitute materials.